

Ava J Tan

List of Publications by Year in descending order

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12
papers

1,054
citations

1040056

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docs citations

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times ranked

1174
citing authors

#	ARTICLE	IF	CITATIONS
1	Electric Field-Induced Permittivity Enhancement in Negative-Capacitance FET. IEEE Transactions on Electron Devices, 2021, 68, 1346-1351.	3.0	10
2	Near Threshold Capacitance Matching in a Negative Capacitance FET With 1 nm Effective Oxide Thickness Gate Stack. IEEE Electron Device Letters, 2020, 41, 179-182.	3.9	30
3	Experimental Demonstration of a Ferroelectric HfO ₂ -Based Content Addressable Memory Cell. IEEE Electron Device Letters, 2020, 41, 240-243.	3.9	45
4	Enhanced ferroelectricity in ultrathin films grown directly on silicon. Nature, 2020, 580, 478-482.	27.8	486
5	Anomalous Beneficial Gate-Length Scaling Trend of Negative Capacitance Transistors. IEEE Electron Device Letters, 2019, 40, 1860-1863.	3.9	16
6	Challenges to Partial Switching of Hf _{0.8} Zr _{0.2} O ₂ Gated Ferroelectric FET for Multilevel/Analog or Low-Voltage Memory Operation. IEEE Electron Device Letters, 2019, 40, 1423-1426.	3.9	27
7	Negative Capacitance FET With 1.8-nm-Thick Zr-Doped HfO ₂ Oxide. IEEE Electron Device Letters, 2019, 40, 993-996.	3.9	106
8	Improved Subthreshold Swing and Short Channel Effect in FDSOI n-Channel Negative Capacitance Field Effect Transistors. IEEE Electron Device Letters, 2018, 39, 300-303.	3.9	128
9	Response Speed of Negative Capacitance FinFETs. , 2018, , .		29
10	Negative Capacitance, n-Channel, Si FinFETs: Bi-directional Sub-60 mV/dec, Negative DIBL, Negative Differential Resistance and Improved Short Channel Effect. , 2018, , .		43
11	Self-Aligned, Gate Last, FDSOI, Ferroelectric Gate Memory Device With 5.5-nm Hf _{0.8} Zr _{0.2} O ₂ , High Endurance and Breakdown Recovery. IEEE Electron Device Letters, 2017, 38, 1379-1382.	3.9	76
12	Stabilization of ferroelectric phase in tungsten capped Hf _{0.8} Zr _{0.2} O ₂ . Applied Physics Letters, 2017, 111, .	3.3	58